

# BC847DS

45 V, 100 mA NPN/NPN general-purpose transistor

Rev. 01 — 25 August 2009

Product data sheet

## 1. Product profile

### 1.1 General description

NPN/NPN general-purpose transistor pair in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

### 1.2 Features

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- No mutual interference between the transistors
- AEC-Q101 qualified

### 1.3 Applications

- General-purpose switching and amplification

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$V_{CE0}$	collector-emitter voltage	open base	-	-	45	V
$I_C$	collector current		-	-	100	mA
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$	200	300	450	

## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1		
2	base TR1		
3	collector TR2		
4	emitter TR2		
5	base TR2		
6	collector TR1		

*sym020*

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BC847DS	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457

## 4. Marking

Table 4. Marking codes

Type number	Marking code
BC847DS	ZL

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

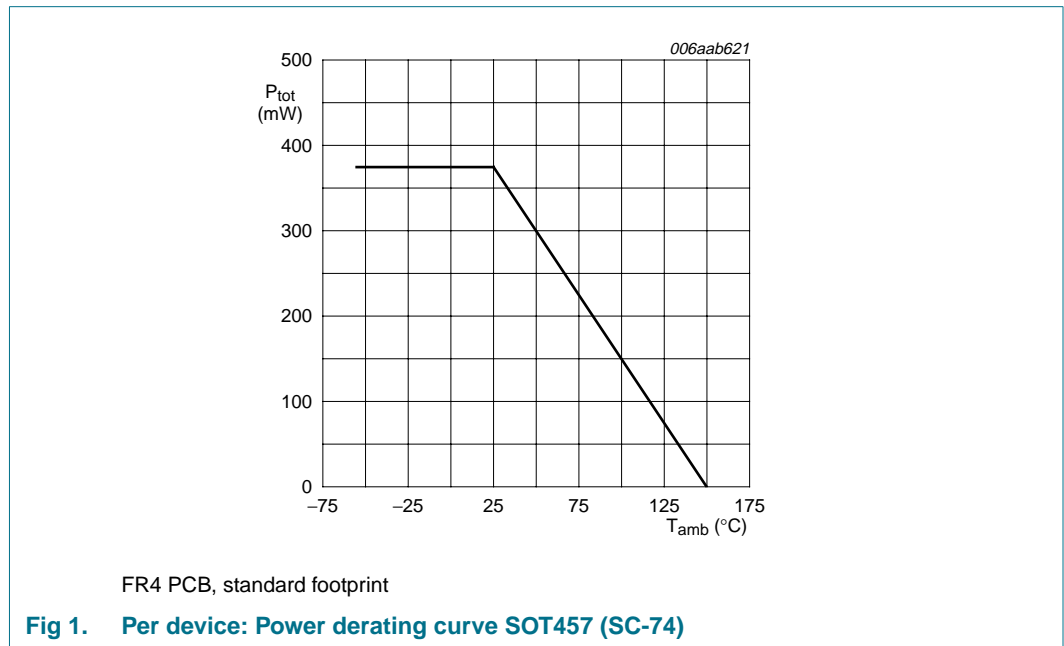
Symbol	Parameter	Conditions	Min	Max	Unit
<b>Per transistor</b>					
$V_{CBO}$	collector-base voltage	open emitter	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	-	45	V
$V_{EBO}$	emitter-base voltage	open collector	-	6	V
$I_C$	collector current		-	100	mA
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	200	mA
$I_{BM}$	peak base current	single pulse; $t_p \leq 1$ ms	-	200	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C	[1]	250	mW
<b>Per device</b>					
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C	[1]	380	mW

**Table 5. Limiting values ...continued**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$T_j$	junction temperature		-	150	°C
$T_{amb}$	ambient temperature		-55	+150	°C
$T_{stg}$	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

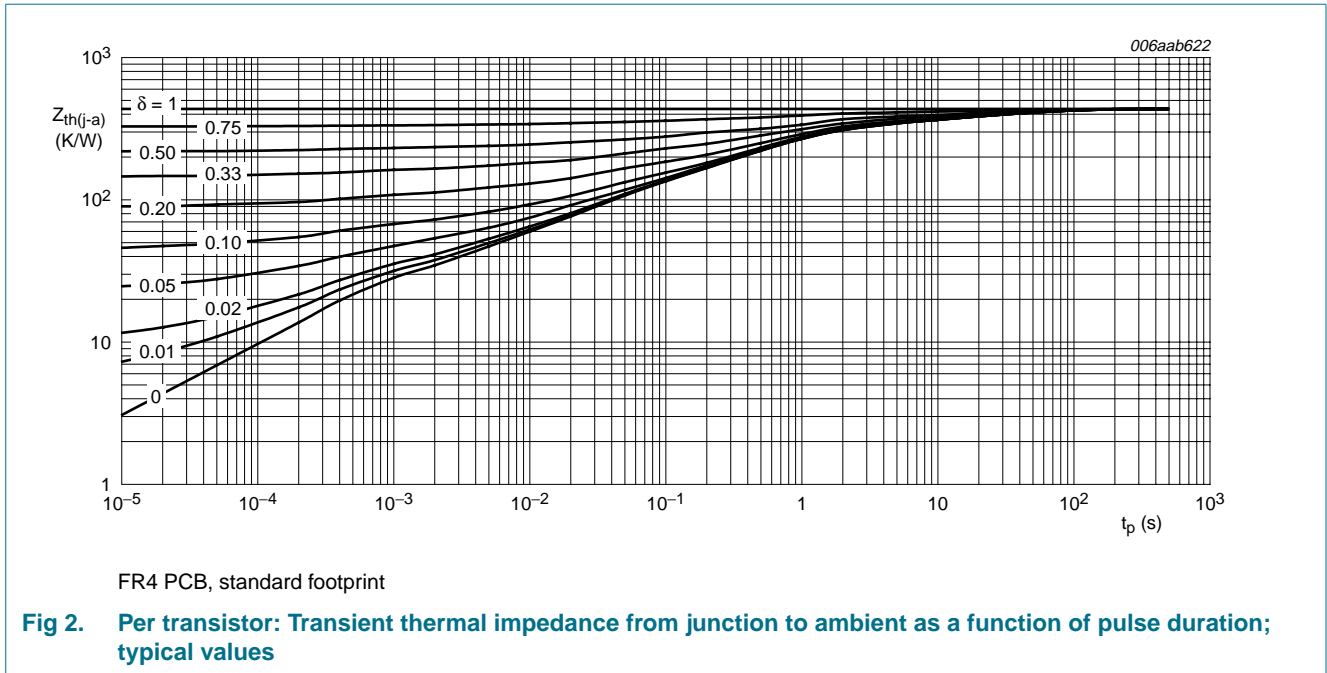


## 6. Thermal characteristics

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	500	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	250	K/W
<b>Per device</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	328	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



## 7. Characteristics

**Table 7. Characteristics**

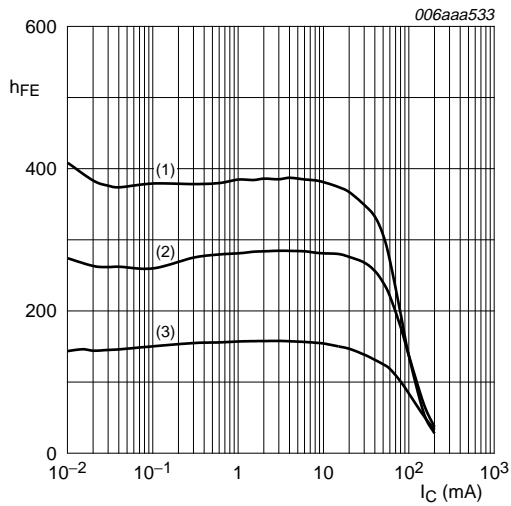
$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 30\text{ V}; I_E = 0\text{ A}$	-	-	15	nA
		$V_{CB} = 30\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	5	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 6\text{ V}; I_C = 0\text{ A}$	-	-	100	nA
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}$				
		$I_C = 10\text{ }\mu\text{A}$	-	280	-	
		$I_C = 2\text{ mA}$	200	300	450	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	55	100	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	-	200	300	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	755	850	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	-	1000	-	mV
$V_{BE}$	base-emitter voltage	$V_{CE} = 5\text{ V}$				
		$I_C = 2\text{ mA}$	580	650	700	mV
		$I_C = 10\text{ mA}$	-	-	770	mV

**Table 7. Characteristics ...continued**

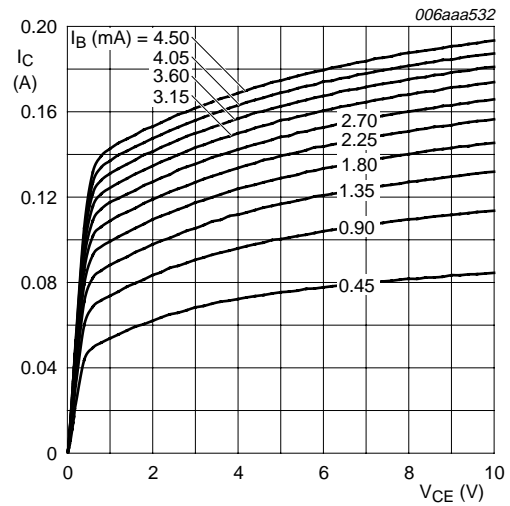
$T_{amb} = 25\text{ }^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}$ ; $I_E = I_e = 0\text{ A}$ ; $f = 1\text{ MHz}$	-	1.9	-	pF
$C_e$	emitter capacitance	$V_{EB} = 0.5\text{ V}$ ; $I_C = I_c = 0\text{ A}$ ; $f = 1\text{ MHz}$	-	11	-	pF
$f_T$	transition frequency	$V_{CE} = 5\text{ V}$ ; $I_C = 10\text{ mA}$ ; $f = 100\text{ MHz}$	100	-	-	MHz
NF	noise figure	$V_{CE} = 5\text{ V}$ ; $I_C = 0.2\text{ mA}$ ; $R_S = 2\text{ k}\Omega$ ; $f = 10\text{ Hz to }15.7\text{ kHz}$	-	1.9	-	dB
		$V_{CE} = 5\text{ V}$ ; $I_C = 0.2\text{ mA}$ ; $R_S = 2\text{ k}\Omega$ ; $f = 1\text{ kHz}$ ; $B = 200\text{ Hz}$	-	3.1	-	dB



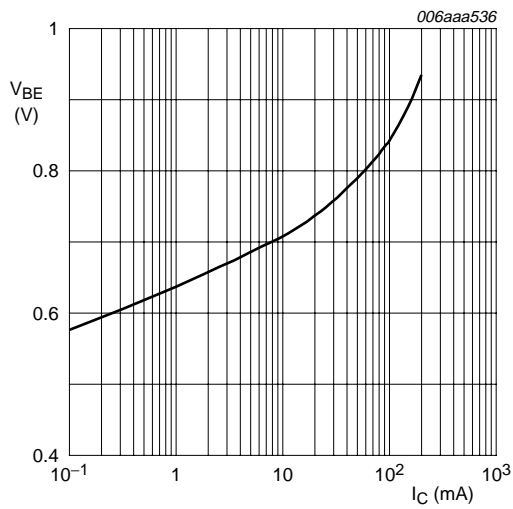
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = 100\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -55\text{ }^\circ\text{C}$

**Fig 3. Per transistor: DC current gain as a function of collector current; typical values**



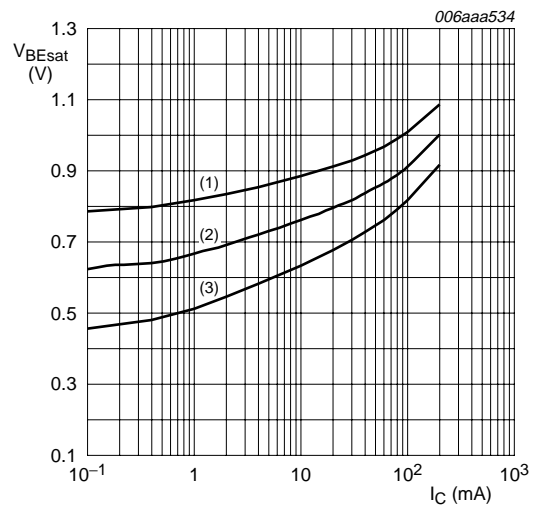
$T_{amb} = 25\text{ }^\circ\text{C}$

**Fig 4. Per transistor: Collector current as a function of collector-emitter voltage; typical values**



$V_{CE} = 5 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

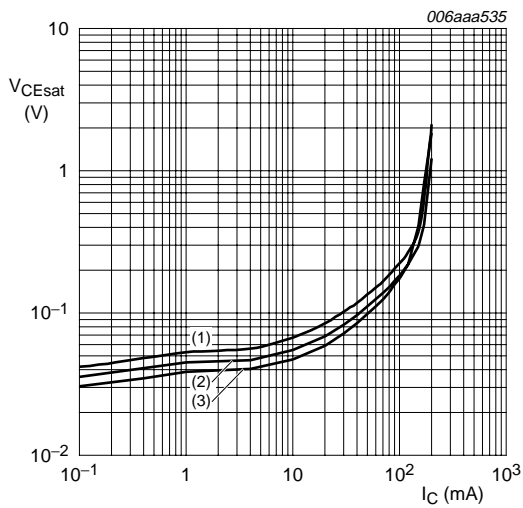
Fig 5. Per transistor: Base-emitter voltage as a function of collector current; typical values



$I_C/I_B = 20$

- (1)  $T_{amb} = -55 \text{ }^\circ\text{C}$
- (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$
- (3)  $T_{amb} = 100 \text{ }^\circ\text{C}$

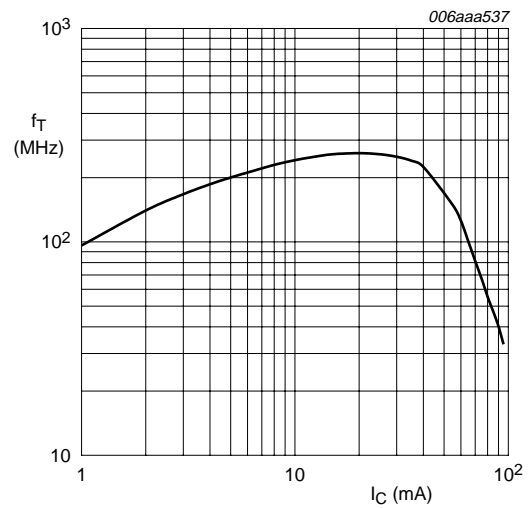
Fig 6. Per transistor: Base-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$

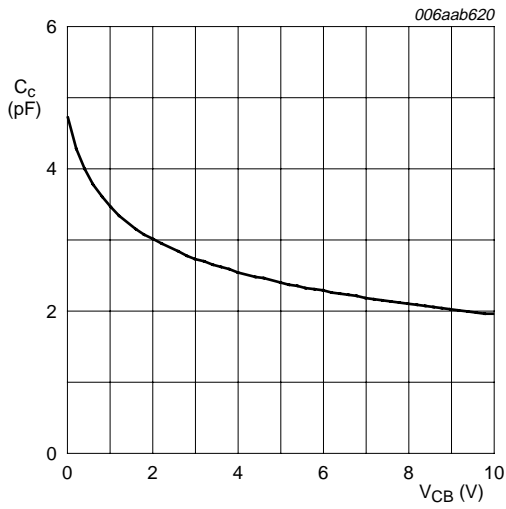
- (1)  $T_{amb} = 100 \text{ }^\circ\text{C}$
- (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$
- (3)  $T_{amb} = -55 \text{ }^\circ\text{C}$

Fig 7. Per transistor: Collector-emitter saturation voltage as a function of collector current; typical values



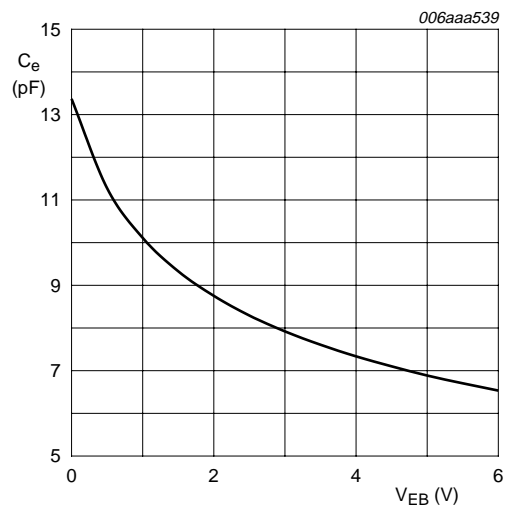
$V_{CE} = 5 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

Fig 8. Per transistor: Transition frequency as a function of collector current; typical values



$f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^\circ\text{C}$

**Fig 9. Per transistor: Collector capacitance as a function of collector-base voltage; typical values**



$f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^\circ\text{C}$

**Fig 10. Per transistor: Emitter capacitance as a function of emitter-base voltage; typical values**

## 8. Test information

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline

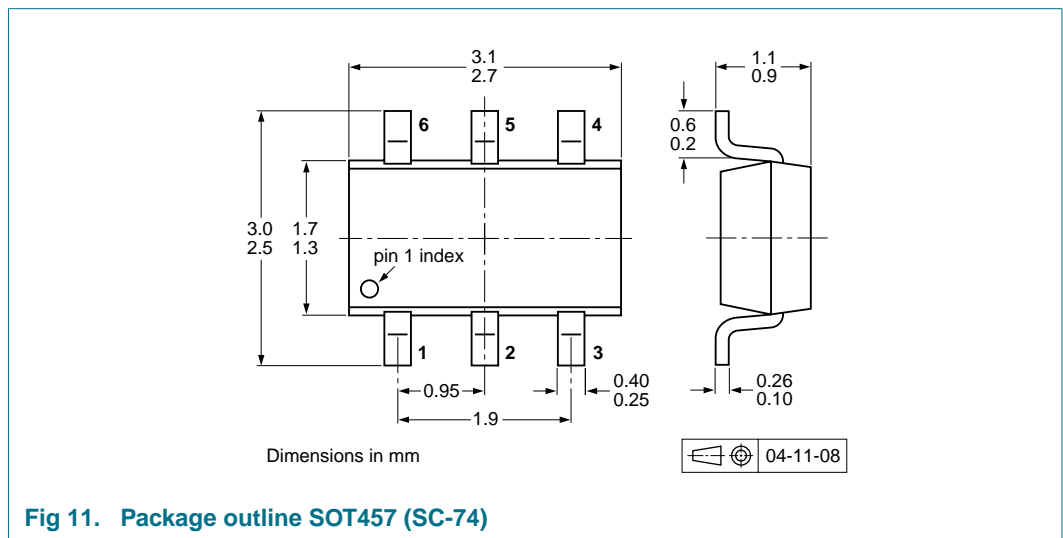


Fig 11. Package outline SOT457 (SC-74)

## 10. Packing information

**Table 8. Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

Type number	Package	Description	Packing quantity	
			3000	10000
BC847DS	SOT457	4 mm pitch, 8 mm tape and reel; T1	<sup>[2]</sup> -115	-135
		4 mm pitch, 8 mm tape and reel; T2	<sup>[3]</sup> -125	-165

[1] For further information and the availability of packing methods, see [Section 14](#).

[2] T1: normal taping

[3] T2: reverse taping



## 11. Soldering

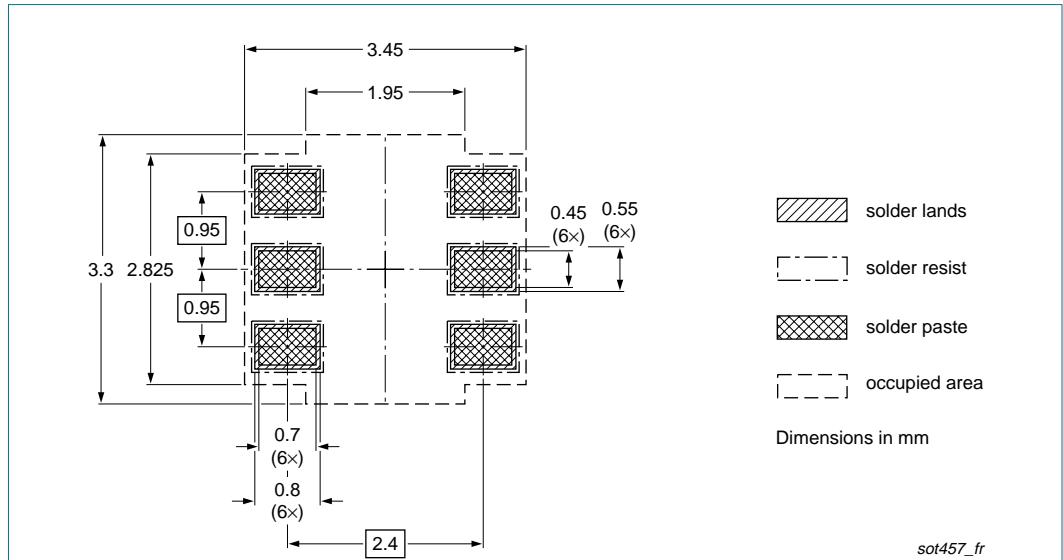


Fig 12. Reflow soldering footprint SOT457 (SC-74)

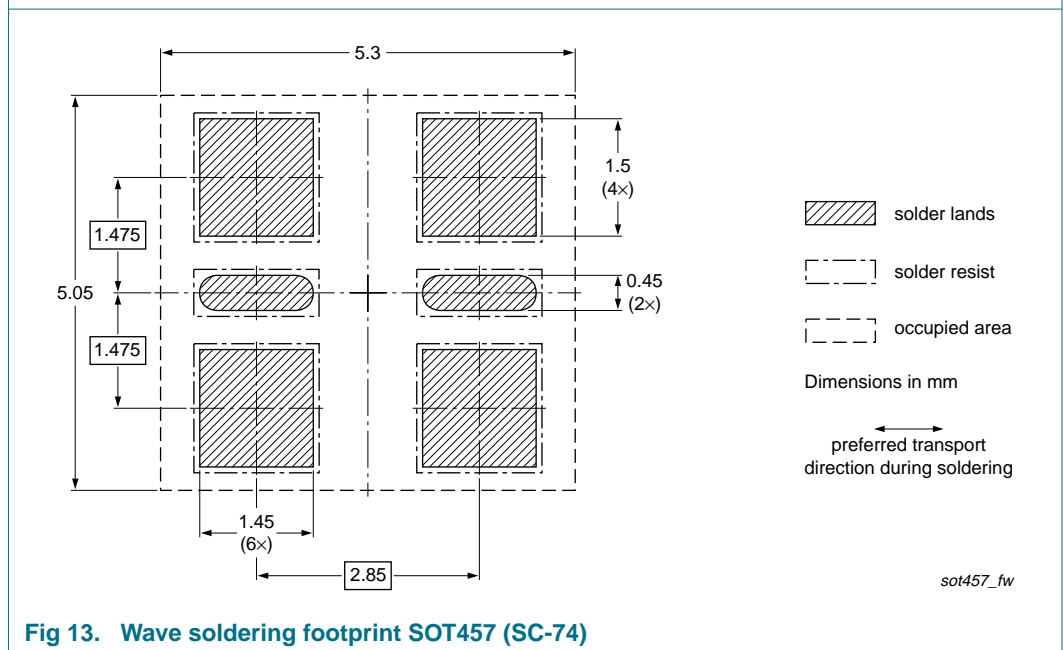


Fig 13. Wave soldering footprint SOT457 (SC-74)

## 12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC847DS_1	20090825	Product data sheet	-	-

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Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[2] The term 'short data sheet' is explained in section "Definitions".

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